# Single SPST Analog Switch

The NLAST4501 is an analog switch manufactured in sub-micron silicon-gate CMOS technology. It achieves very low  $R_{ON}$  while maintaining extremely low power dissipation. The device is a bilateral switch suitable for switching either analog or digital signals, which may vary from zero to full supply voltage.

The NLAST4501 is a low voltage, TTL (low threshold) compatible device, pin for pin compatible with the MAX4501.

The Enable pin is compatible with standard TTL level outputs when supply voltage is nominal 5.0 Volts. It is also over-voltage tolerant, making it a very useful logic level translator.

- Guaranteed  $R_{ON}$  of 32  $\Omega$  at 5.5 V
- Low Power Dissipation:  $I_{CC} = 2 \mu A$
- Low Threshold Enable pin TTL compatible at 5.0 Volts
- TTL version and pin for pin with NLAS4501
- Provides Voltage translation for many different voltage levels
  - 3.3 to 5.0 Volts, Enable pin may go as high as +5.5 Volts
  - 1.8 to 3.3 Volts
  - 1.8 to 2.5 Volts
- Improved version of MAX4501 (at any voltage between 2 and 5.5 Volts)
- Chip Complexity: FETs = 11

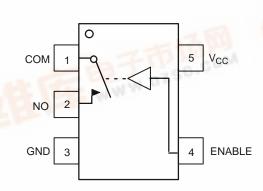
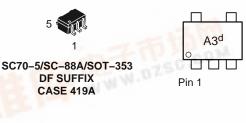


Figure 1. Pinout (Top View)



,24小时加急出货

MARKING DIAGRAMS





专业PCB打样工厂



SOT23-5/TSOP-5/SC59-5 DT SUFFIX CASE 483

d = Date Code

## PIN ASSIGNMENT

Pin	Function
1	СОМ
2	NO
3	GND
4	ENABLE
5	V <sub>CC</sub>

#### FUNCTION TABLE

State of Analog Switch
Off
On

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 8 of this data sheet.



#### **MAXIMUM RATINGS**

Symbol		Parameter	Value	Unit
V <sub>CC</sub>	Positive DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	Digital Input Voltage (Enable)		-0.5 to +7.0	V
V <sub>IS</sub>	Analog Output Voltage ( $V_{NO}$ or $V_{CON}$	n)	-0.5 to V <sub>CC</sub> $+0.5$	V
I <sub>IK</sub>	DC Current, Into or Out of Any Pin		±20	mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150	°C	
TL	Lead Temperature, 1 mm from Case	for 10 Seconds	260	°C
TJ	Junction Temperature under Bias		+ 150	°C
$\theta_{JA}$	Thermal Resistance	SC70–5/SC–88A (Note 1) TSOP–5	350 230	°C/W
P <sub>D</sub>	Power Dissipation in Still Air at 85°C	SC70–5/SC–88A TSOP–5	150 200	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% – 35%	UL-94-VO (0.125 in)	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 100 N/A	V
I <sub>Latch-Up</sub>	Latch–Up Performance	Above $V_{CC}$ and Below GND at 85°C (Note 5)	±300	mA

Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.

2. Tested to EIA/JESD22-A114-A.

3. Tested to EIA/JESD22-A115-A.

4. Tested to JESD22-C101-A.

5. Tested to EIA/JESD78.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	Positive DC Supply Voltage		2.0	5.5	V
V <sub>IN</sub>	Digital Input Voltage (Enable)		GND	5.5	V
V <sub>IO</sub>	Static or Dynamic Voltage Across an Off Switch		GND	V <sub>CC</sub>	V
V <sub>IS</sub>	Analog Input Voltage (NO, COM)		GND	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range, All Package Types		- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise or Fall Time, (Enable Input)	$\begin{array}{l} {\sf V}_{cc} = 3.3 \; {\sf V} \; \pm \; 0.3 \; {\sf V} \\ {\sf V}_{cc} = 5.0 \; {\sf V} \; \pm \; 0.5 \; {\sf V} \end{array}$	0 0	100 20	ns/V

#### DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

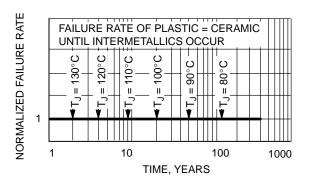


Figure 2. Failure Rate vs. Time Junction Temperature

# DC CHARACTERISTICS – Digital Section (Voltages Referenced to GND)

				Guaranteed Max Limit			
Symbol	Parameter	Condition	V <sub>cc</sub>	−55°C to 25°C	<85°C	<125°C	Unit
VIH	Minimum High-Level Input		3.0	1.4	1.4	1.4	V
	Voltage, Enable Inputs		4.5	2.0	2.0	2.0	
			5.5	2.0	2.0	2.0	
V <sub>IL</sub>	Maximum Low-Level Input		3.0	0.53	0.53	0.53	V
	Voltage, Enable Inputs		4.5	0.8	0.8	0.8	
			5.5	0.8	0.8	0.8	
I <sub>IN</sub>	Maximum Input Leakage Current, Enable Inputs	$V_{IN} = 5.5 V \text{ or GND}$	0 V to 5.5 V	±0.1	±1.0	±1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current	Enable and VIS = $V_{CC}$ or GND	5.5	1.0	1.0	2.0	μΑ
	(per package)						

### DC ELECTRICAL CHARACTERISTICS – Analog Section

				Guaranteed Max Limit		nit	
Symbol	Parameter	Condition	V <sub>CC</sub>	−55°C to 25°C	<85°C	<125°C	Unit
R <sub>ON</sub>	Maximum ON Resistance	$V_{IN} = V_{IH}$	3.0	45	50	55	Ω
	(Figures 8 – 12)	$V_{IS} = V_{CC}$ to GND	4.5	30	35	40	
		$I_{IS}I = \le 10.0 \text{ mA}$	5.5	25	30	35	
R <sub>FLAT(ON)</sub>	ON Resistance Flatness	$V_{IN} = V_{IH}$ $I_{IS}I = \le 10.0 \text{ mA}$ $V_{IS} = 1 \text{ V}, 2 \text{ V}, 3.5 \text{ V}$	4.5	4	4	5	Ω
I <sub>NO(OFF)</sub>	Off Leakage Current, Pin 2 (Figure 3)		5.5	1	10	100	nA
I <sub>COM(OFF)</sub>	Off Leakage Current, Pin 1 (Figure 3)	V <sub>IN</sub> = V <sub>IL</sub> V <sub>NO</sub> = 4.5 V or 1.0 V V <sub>COM</sub> = 1.0 V or 4.5 V	5.5	1	10	100	nA

# AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$ )

					Guaranteed Max Limit								
			$v_{cc}$	- 55	°C to 2	25°C		<85°C	;	•	<125°0	0	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
t <sub>ON</sub>	Turn–On Time	$R_L = 300 \Omega, C_L = 35 pF$	2.0		7.0	14			16			16	ns
		(Figures 4, 5, and 13)	3.0		5.0	10			12			12	
			4.5		4.5	9			11			11	
			5.5		4.5	9			11			11	
tOFF	Turn–Off Time	$R_L = 300 \Omega, C_L = 35 pF$	2.0		11.0	22			24			24	ns
		(Figures 4, 5, and 13)	3.0		7.0	14			16			16	
			4.5		5.0	10			12			12	
			5.5		5.0	10			12			12	

		Typical @ 25, VCC = 5.0 V	
C <sub>IN</sub>	Maximum Input Capacitance, Select Input	8	pF
C <sub>NO or</sub> C <sub>NC</sub>	Analog I/O (switch off)	10	
C <sub>COM(OFF)</sub>	Common I/O (switch off)	10	
C <sub>COM(ON)</sub>	Feedthrough (switch on)	20	

			V <sub>CC</sub>	Limit	
Symbol	Parameter	Condition	v	25°C	Unit
BW	Maximum On-Channel -3dB Bandwidth	V <sub>IS</sub> = 0 dBm	3.0	190	MHz
	or Minimum Frequency Response	$V_{\text{IS}}$ centered between $V_{\text{CC}}$ and GND	4.5	200	
		(Figures 6 and 14)	5.5	220	
V <sub>ONL</sub>	Maximum Feedthrough On Loss	V <sub>IS</sub> = 0 dBm @ 10 kHz	3.0	-2	dB
		$V_{\text{IS}}$ centered between $V_{\text{CC}}$ and GND	4.5	-2	
		(Figure 6)	5.5	-2	
V <sub>ISO</sub>	Off-Channel Isolation	f = 100 kHz; V <sub>IS</sub> = 1 V RMS	3.0	- 93	dB
		$V_{\text{IS}}$ centered between $V_{\text{CC}}$ and GND	4.5		
		(Figures 6 and 15)	5.5		
Q	Charge Injection	$V_{IS} = V_{CC}$ to GND, $F_{IS} = 20$ kHz	3.0	1.5	рС
	Enable Input to Common I/O	$t_r = t_f = 3 \text{ ns}$	5.5	3.0	
		$R_{IS} = 0 \ \Omega, \ C_{L} = 1000 \ pF$			
		$Q = C_L * \Delta V_{OUT}$			
		(Figures 7 and 16)			
THD	Total Harmonic Distortion	$F_{IS}$ = 20 Hz to 1 MHz, $R_L$ = Rgen = 600 $\Omega,C_L$ = 50 pF	3.3	0.3	%
	THD + Noise	$V_{IS} = 3.0 V_{PP}$ sine wave	5.5	0.15	
		$V_{IS} = 5.0 V_{PP}$ sine wave			
		(Figure 17)			

### ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

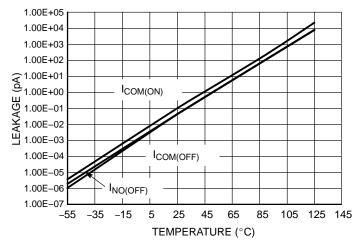
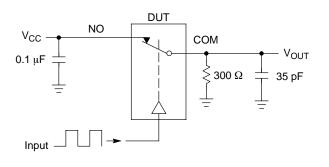


Figure 3. Switch Leakage vs. Temperature



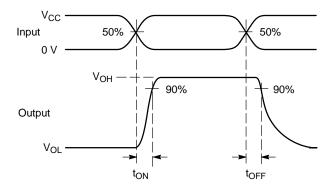
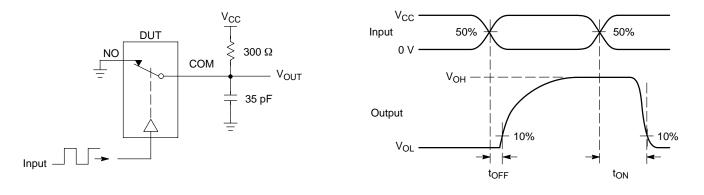
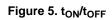
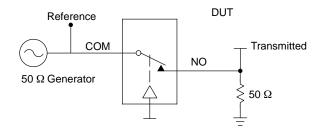


Figure 4. t<sub>ON</sub>/t<sub>OFF</sub>







Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch.  $V_{ISO}$ , Bandwidth and  $V_{ONL}$  are independent of the input signal direction.

$$\begin{split} V_{ISO} &= Off \ Channel \ Isolation = 20 \ Log \ \left(\frac{VOUT}{V_{IN}}\right) \ for \ V_{IN} \ at \ 100 \ kHz \\ V_{ONL} &= On \ Channel \ Loss = 20 \ Log \ \left(\frac{VOUT}{V_{IN}}\right) \ for \ V_{IN} \ at \ 100 \ kHz \ to \ 50 \ MHz \\ Bandwidth \ (BW) &= the \ frequency \ 3 \ dB \ below \ V_{ONL} \end{split}$$

#### Figure 6. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V<sub>ONL</sub>

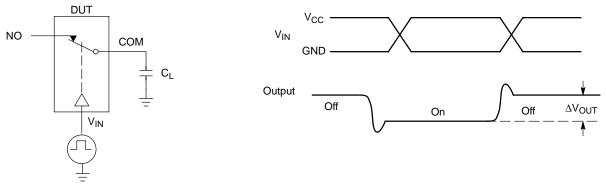
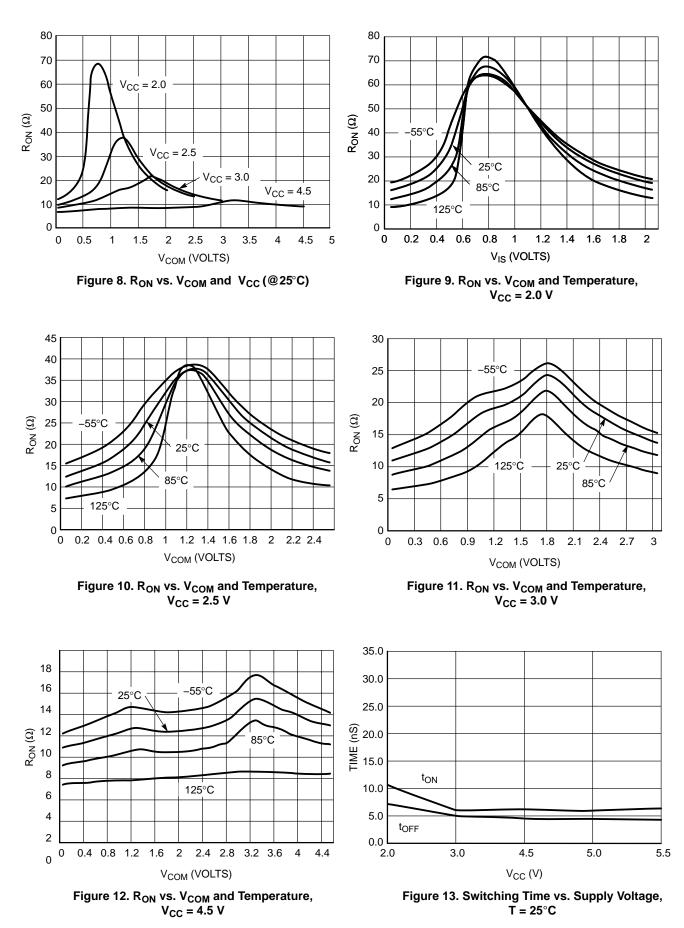
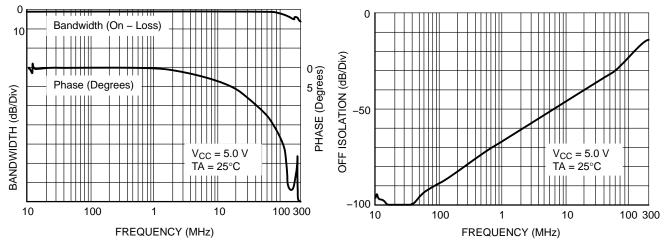


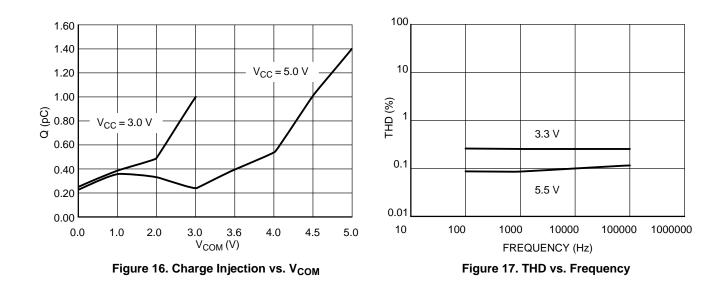
Figure 7. Charge Injection: (Q)











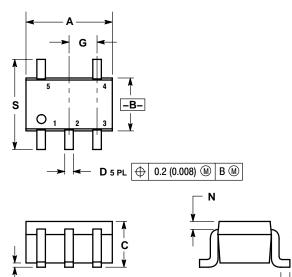
#### **DEVICE ORDERING INFORMATION**

		Device	Nomenclatu				
Device Order Number	Circuit Indicator	Technology	Device Function	Package Suffix	Tape & Reel Suffix	Package Type (Name/SOT#/ Common Name)	Tape & Reel Size
NLAST4501DFT2	NL	AST	4501	DF	T2	SC70–5/SC–88A/ SOT–353	178 mm (7 in) 3000 Unit
NLAST4501DTT1	NL	AST	4501	DT	T1	SOT23-5/TSOP-5/ SC59-5	178 mm (7 in) 3000 Unit

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

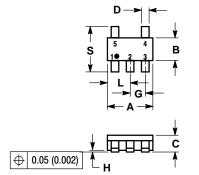
#### PACKAGE DIMENSIONS

SC-88A/SOT-353 **DF SUFFIX** CASE 419A-02 ISSUE G

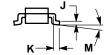


TSOP-5 **DT SUFFIX** CASE 483-02 ISSUE C

κ



н



- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INC	HES	MILLIM	ETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	D 0.004 0.012		0.10	0.30	
G	0.026	BSC	0.65	BSC	
Н		0.004		0.10	
J	0.004	0.010	0.10	0.25	
Κ	0.004	0.012	0.10	0.30	
Ν	0.008	REF	0.20	REF	
S	0.079	0.087	2.00	2.20	

- NOTES: 1. DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
  A AND B DIMENSIONS DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.1142	0.1220
В	1.30	1.70	0.0512	0.0669
С	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.05	0.0335	0.0413
н	0.013	0.100	0.0005	0.0040
J	0.10	0.26	0.0040	0.0102
К	0.20	0.60	0.0079	0.0236
L	1.25	1.55	0.0493	0.0610
м	0	10	0	10
S	2.50	3.00	0.0985	0.1181

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any provided in SCILLC data sheets and/or specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product cand its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use papication SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for esale in any manner.

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2–9–1 Kamimeguro, Meguro–ku, Tokyo, Japan 153–0051 Phone: 81–3–5773–3850 ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.